

PHOTO INTERRUPTERS

PS4001, PS4003, PS4005, PS4007, PS4009

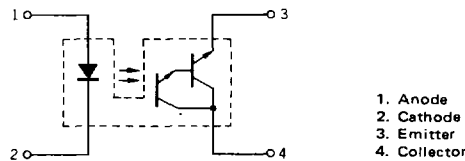
PHOTO INTERRUPTER

NEPOC SERIES

DESCRIPTION

The PS4001, PS4003, PS4005, PS4007, PS4009 are photo coupled interrupter modules containing a GaAs light emitting diode and an NPN silicon darlington connected photo-transistor.

CONNECTION DIAGRAM (Top View)



ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Diode

Reverse Voltage	V_R	5.0	V
Forward Current	I_F	50	mA
Power Dissipation	P_D	100	mW

Transistor

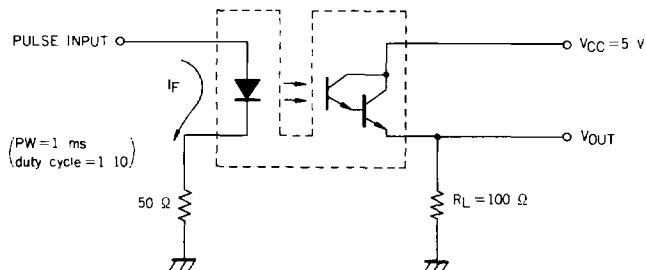
Collector to Emitter Voltage	V_{CEO}	30	V
Collector Current	I_C	50	mA
Power Dissipation	P_C	100	mW
Storage Temperature	T_{stg}	-40 to +100	°C
Operating Temperature	T_{opt}	-20 to +80	°C

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

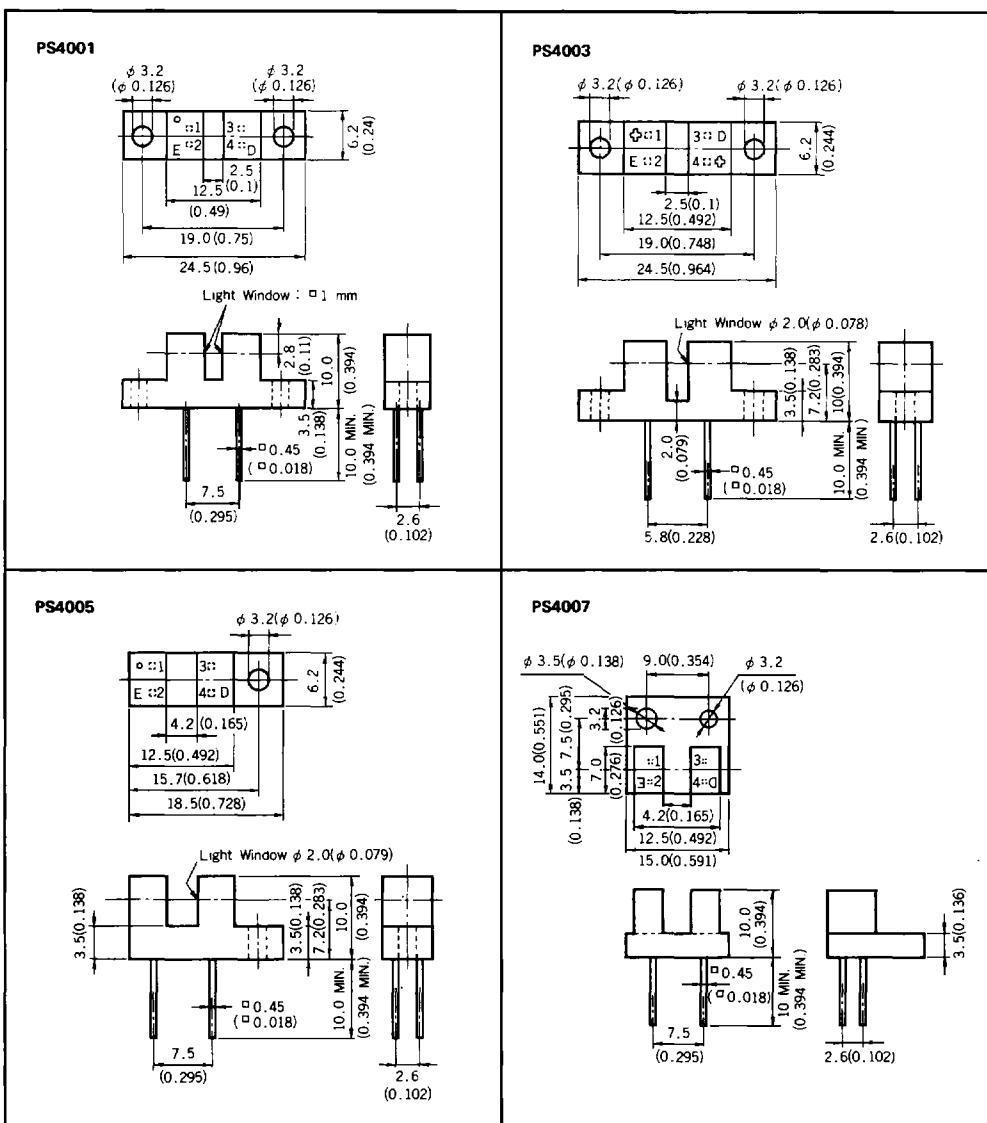
CHARACTERISTIC		SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Diode	Forward Voltage	V_F		1.1	1.4	V	$I_F = 20 \text{ mA}$
	Reverse Current	I_R			20	μA	$V_R = 4.0 \text{ V}$
	Junction Capacitance	C		100		pF	$V = 0, f = 1.0 \text{ MHz}$
Transistor	Collector to Emitter Dark Current	I_{CEO}			400	nA	$V_{CE} = 10 \text{ V}, I_F = 0$
Coupled	Current Transfer Ratio	$CTR(I_C/I_F)$	20*			%	$I_F = 10 \text{ mA}, V_{CE} = 2.0 \text{ V}$
	Collector Saturation Voltage	$V_{CE(sat)}$			1.2	V	$I_F = 10 \text{ mA}, I_C = 0.5 \text{ mA}$
	Rise Time	t_r		200		μs	$V_{CC} = 5.0 \text{ V}, I_C = 2.0 \text{ mA}, R_L = 100 \Omega$ *
	Fall Time	t_f		200		μs	$V_{CC} = 5.0 \text{ V}, I_C = 2.0 \text{ mA}, R_L = 100 \Omega$ *

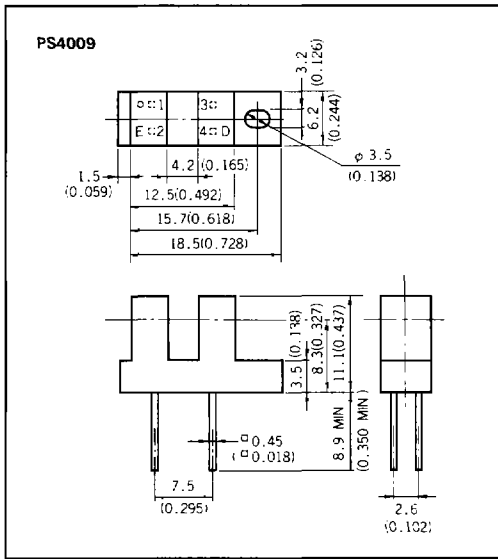
* PS4003 : 15 % MIN., Others : 20 % MIN.

* Test Circuit for Switching Time

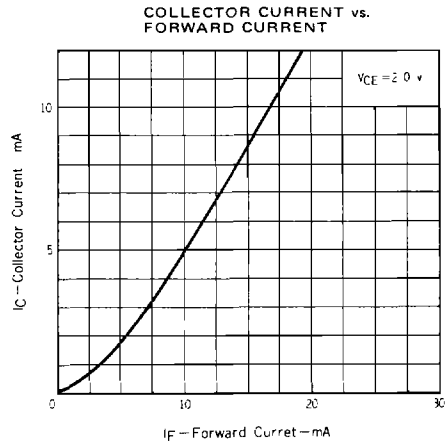
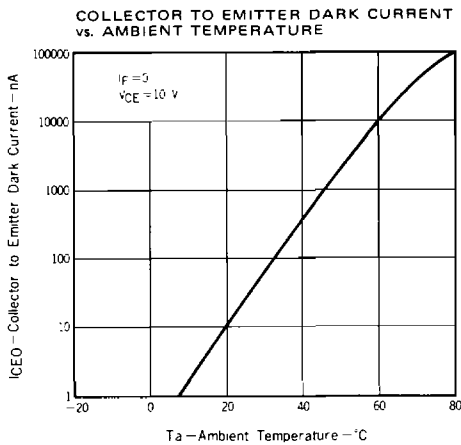
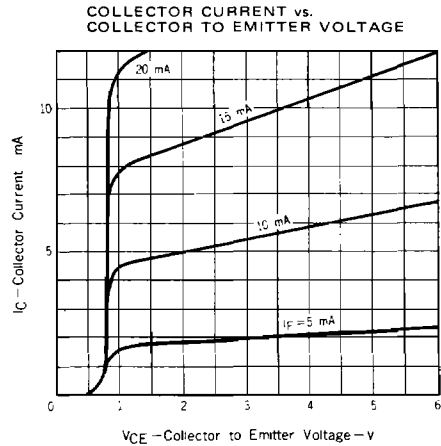
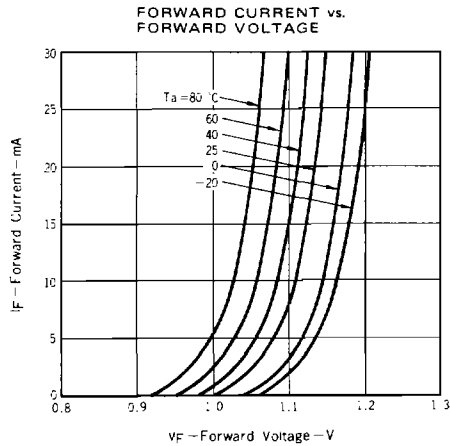


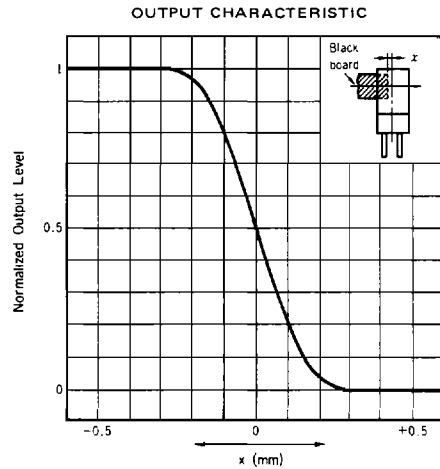
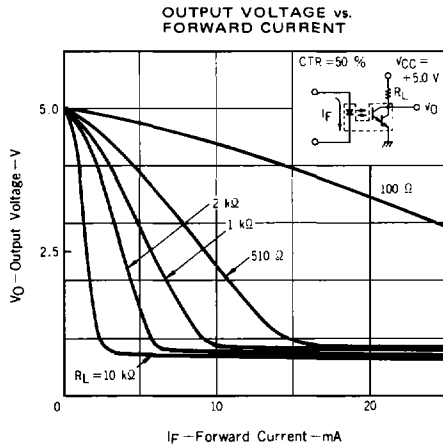
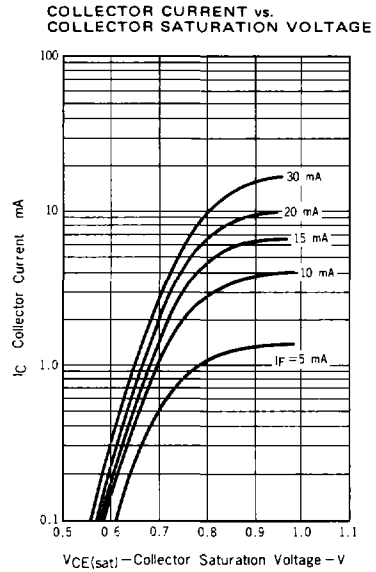
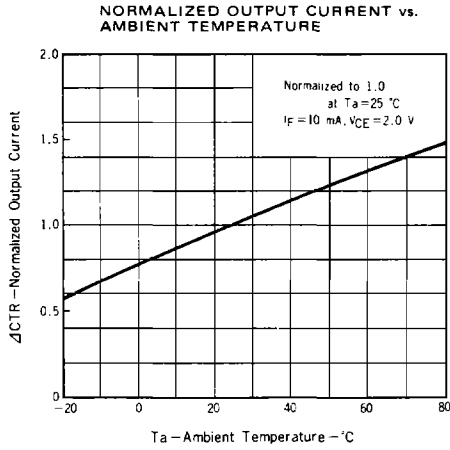
PACKAGE DIMENSIONS
in millimeters (inches)





TYPICAL CHARACTERISTICS (Ta = 25 °C)





TYPICAL APPLICATION

